Supporting Materials

Differentiation of Gas Molecules Using Flexible and All-Carbon Nanotube Devices

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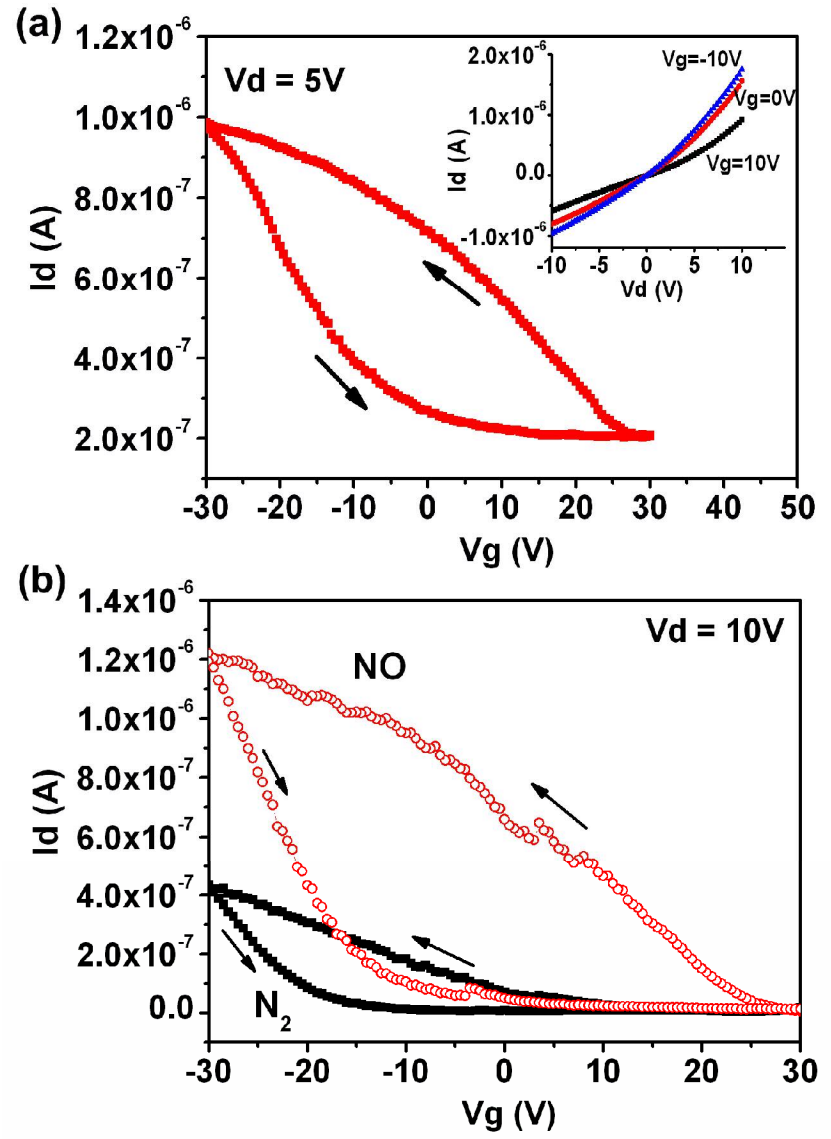
Figure summary:

Figure S1. (a) Typical electrical characteristics including transfer curves and I_d - V_d relations for an all-P2-SWNT transistor. (b) Transfer curves showing that an all-P2-SWNT transistor is *p*-doped (or threshold voltage positively shifted) upon exposure to NO from N_2.

Figure S2. Typical electrical characteristics, I_d vs. V_g and I_d vs. V_d for an all-P3-SWNT resistor. The resistance of the resistor is 0.51MΩ.

Figure S3. Sensing curves for the Au-contacted resistor showing that the device is normally insensitive to CO exposure (measured at V_d = 10V).



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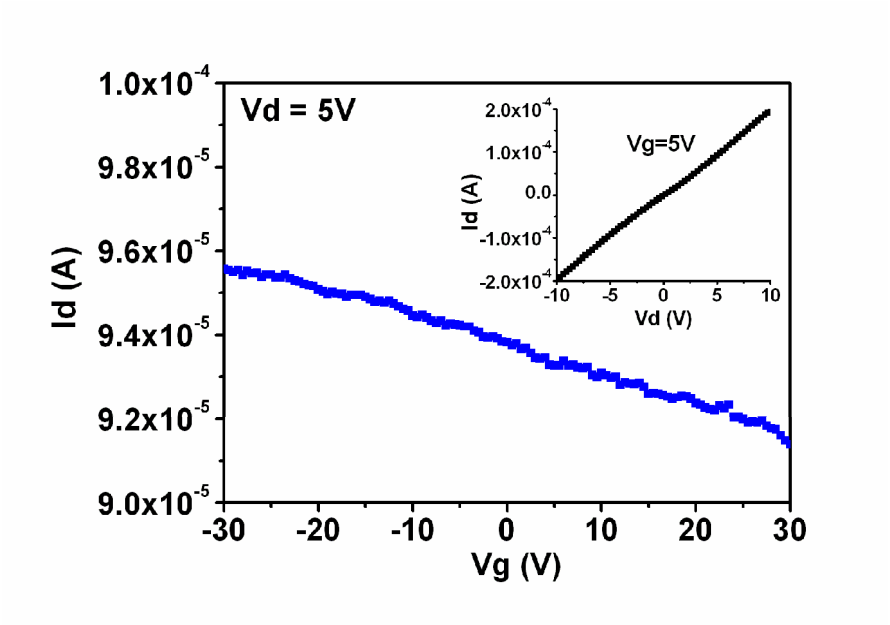

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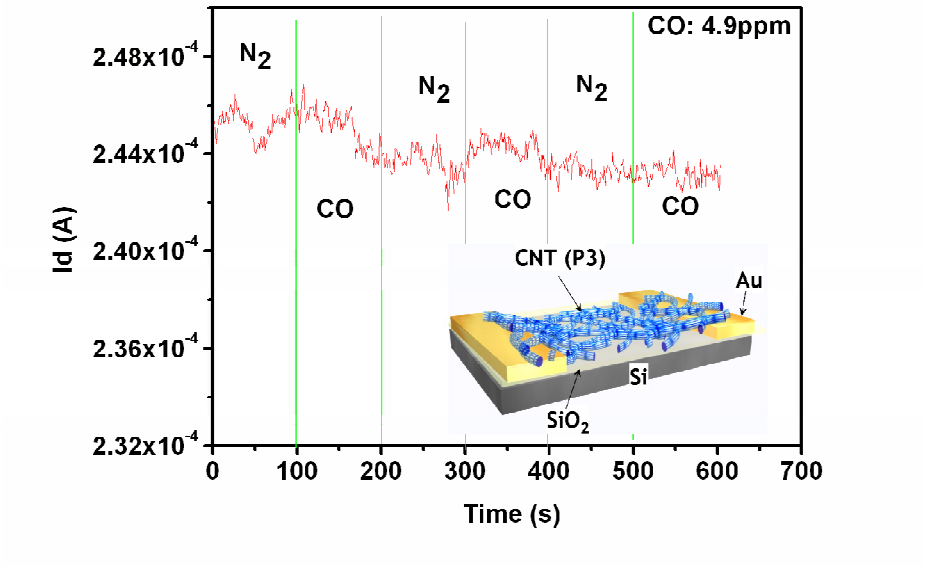

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